

1     **ABSTRACT OF THE DISCLOSURE**

2             In one aspect, the invention encompasses a method of utilizing a  
3     vaporization surface as an electrode to form a plasma within a vapor  
4     forming device. In another aspect, the invention encompasses a method  
5     of chemical vapor deposition. A vaporization surface is provided and  
6     heated. At least one material is flowed past the heated surface to  
7     vaporize the material. A deposit forms on the vaporization surface  
8     during the vaporization. The vaporization surface is then utilized as an  
9     electrode to form a plasma, and at least a portion of the deposit is  
10    removed with the plasma. In another aspect, the invention encompasses  
11    a vapor forming device. Such device includes a non-vapor-state-material  
12    input region, a vaporization surface, and a flow path between the non-  
13    vapor-state-material input region and the vaporization surface. The  
14    device further includes a vapor-state-material output region, and a vapor  
15    flow path from the vaporization surface to the vapor-state-material output  
16    region. Additionally, the device includes a first plasma electrode spaced  
17    from the vaporization surface, and plasma generation circuitry configured  
18    to utilize the vaporization surface as a second plasma electrode such that  
19    a plasma can be formed between the first and second plasma electrodes.

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